

AMENDMENTS TO THE CLAIMS

1-5 (Canceled).

6. (Previously presented) A method for fabricating a CMOS image sensor, comprising:

a) providing a semiconductor structure, wherein the semiconductor structure includes an impurity region and a gate electrode;

b) forming a first spacer on a first sidewall of the gate electrode and a fourth spacer on a second side wall of the gate electrode, wherein the first spacer is overlapped with a portion of the impurity region; and

c) removing the fourth spacer by a photo resist pattern covering the impurity region and the first spacer; and

d) forming a second spacer on a sidewall of the first spacer and a third spacer on a second sidewall of the gate electrode.

7. (Original) The method as recited in claim 6, comprising:

b1) forming a first oxide layer on the semiconductor structure; and

b2) carrying out an etching process to form the first spacer.

8. (Original) The method as recited in claim 7, comprising forming the first oxide layer by carrying out a thermal oxidation process.

9. (Canceled)

10. (Previously presented) The method as recited in claim 7, comprising:

c1) forming a photoresist pattern covering the impurity region and the first spacer;

- c2) carrying out an etching process to remove the fourth spacer;
- c3) removing the photoresist pattern;
- c4) forming a second oxide layer on a resulting substrate; and
- c5) carrying out an etching process to form the second spacer and the third spacer.

11. (Original) The method as recited in claim 10, comprising forming the second oxide layer by carrying out a thermal oxidation process.

12. (Original) The method as recited in claim 6, wherein the impurity region is an N-type.

13. (Original) The method as recited in claim 12, additionally comprising:

d) carrying an ion implantation to form a P-type impurity region on the impurity region to thereby obtain a photodiode; and

e) forming a floating diffusion region spaced away from the impurity region by a predetermined distance.

14 – 18 (Canceled).